

HIGH COUPLING FLOATING GATE TRANSISTOR

ABSTRACT OF THE DISCLOSURE

The present invention provides methods of fabricating floating gate transistors. One method includes forming laterally spaced source and drain regions to define a channel therebetween, forming a first floating gate portion above the channel region, the first floating gate portion extending in a general horizontal direction, forming spacers over the first floating gate portion to define an exposed region on the first floating gate portion, forming a contact coupled to the first floating gate portion at the exposed region, the contact extending vertically above the first portion, forming a second floating gate portion coupled to the contact, the second floating gate portion extending in a general vertical direction, and forming a control gate adjacent to the second portion.